

VN2410

N-Channel Enhancement-Mode Vertical DMOS FET

Features

- · Free from Secondary Breakdown
- Low Power Drive Requirement
- · Ease of Paralleling
- Low C_{ISS} and Fast Switching Speeds
- Excellent Thermal Stability
- Integral Source-Drain Diode
- · High Input Impedance and High Gain

Applications

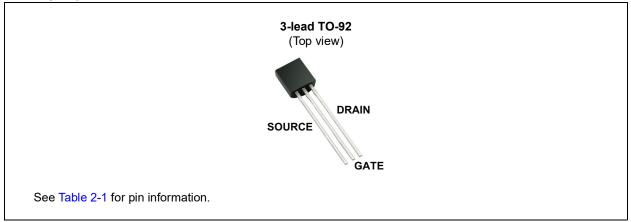
- Motor Controls
- Converters
- Amplifiers
- Switches
- Power Supply Circuits
- Drivers (Relays, Hammers, Solenoids, Lamps, Memories, Displays, Bipolar Transistors, etc.)

General Description

The VN2410 Enhancement-mode (normally-off) transistors use a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited for a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Package Type



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1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

| Drain-to-Source Voltage | BV _{DSS} |
|---|-------------------|
| Drain-to-Gate Voltage | |
| Gate-to-Source Voltage | |
| Operating Ambient Temperature, T _A | |
| Storage Temperature, T _S | |

† Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Electrical Specifications: T_A = 25°C unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. Pulse test: 300 µs pulse, 2% duty cycle

| Parameter | Sym. | Min. | Тур. | Max. | Unit | Conditions | | | |
|--|---------------------|------|------|------|------|---|--|--|--|
| Drain-to-Source Breakdown Voltage | BV _{DSS} | 240 | | | V | V _{GS} = 0V, I _D = 100 μA | | | |
| Gate Threshold Voltage | V _{GS(th)} | 0.8 | _ | 2 | V | $V_{GS} = V_{DS}$, $I_D = 1 \text{ mA}$ | | | |
| Gate Body Leakage Current | I _{GSS} | | — | 100 | nA | V _{GS} = 20V, V _{DS} = 0V | | | |
| | | | _ | 10 | μA | V _{GS} = 0V, V _{DS} = 120V | | | |
| Zero-Gate Voltage Drain Current | I _{DSS} | | _ | 500 | μA | V _{GS} = 0V, V _{DS} = 120V, T _A = 125°C (Note 1) | | | |
| On-State Drain Current | I _{D(ON)} | 1 | _ | _ | А | V _{GS} = 10V, V _{DS} = 15V | | | |
| Static Drain-to-Source On-State Resistance | D | | _ | 10 | Ω | V _{GS} = 2.5V, I _D = 100 mA | | | |
| | R _{DS(ON)} | | — | 10 | Ω | V _{GS} = 10V, I _D = 500 mA | | | |
| Change in $R_{DS(ON)}$ with Temperature | $\Delta R_{DS(ON)}$ | _ | 1 | 1.4 | %/°C | V _{GS} = 10V, I _D = 500 mA (Note 1) | | | |

Note 1: Specification is obtained by characterization and is not 100% tested.

AC ELECTRICAL CHARACTERISTICS

| Electrical Specifications: T _A = 25°C unless otherwise specified. All AC parameters are not 100% sample tested. | | | | | | | | | |
|--|--------------------|------|------|------|------|--|--|--|--|
| Parameter | Sym. | Min. | Тур. | Max. | Unit | Conditions | | | |
| Forward Transconductance | G _{FS} | 300 | | | mmho | V _{DS} = 10V, I _D = 500 mA | | | |
| Input Capacitance | C _{ISS} | _ | _ | 125 | pF | V _{GS} = 0V, | | | |
| Common-Source Output Capacitance | C _{OSS} | _ | _ | 50 | pF | $V_{\rm DS} = 25V,$ | | | |
| Reverse Transfer Capacitance | C _{RSS} | — | _ | 20 | pF | f = 1 MHz | | | |
| Turn-On Delay Time | t _{d(ON)} | _ | _ | 8 | ns | | | | |
| Rise Time | t _r | _ | _ | 8 | ns | $V_{DD} = 60V,$ | | | |
| Turn-Off Delay Time | | — | | 23 | ns | I _D = 400 mA, R _{GEN} = 25Ω | | | |
| Fall Time | t _f | _ | _ | 24 | ns | GEN | | | |
| DIODE PARAMETER | | | | | | | | | |
| Diode Forward Voltage Drop | V _{SD} | — | 1.2 | | V | V _{GS} = 0V, I _{SD} = 190 mA (Note 1) | | | |
| | | | | | | | | | |

Note 1: Unless otherwise stated, all DC parameters are 100% tested at 25°C. Pulse test: 300 µs pulse, 2% duty cycle

TEMPERATURE SPECIFICATIONS

| Sym. | Min. | Тур. | Max. | Unit | Conditions | | |
|-------------------|----------------------------------|--|--|--|--|--|--|
| TEMPERATURE RANGE | | | | | | | |
| T _A | -55 | — | +150 | °C | | | |
| Τ _S | -55 | _ | +150 | °C | | | |
| | | | | | | | |
| θ_{JA} | — | 132 | | °C/W | | | |
| | T _A T _S | T _A -55 T _S -55 | T _A -55 - T _S -55 - | T _A -55 - +150 T _S -55 - +150 | T _A -55 - +150 °C T _S -55 - +150 °C | | |

THERMAL CHARACTERISTICS

| Package | I _D (Note 1) (Continuous) (mA) | I _D (Pulsed) (A) | Power Dissipation at T _A = 25°C (W) | I _{DR} (Note 1) (mA) | I _{DRM} (A) |
|--------------|---|-----------------------------------|--|----------------------------------|-------------------------|
| 3-lead TO-92 | 190 | 1.7 | 1 | 190 | 1.7 |

Note 1: I_D (continuous) is limited by maximum rated T_J .

2.0 PIN DESCRIPTION

The details on the pins of VN2410 are listed in Table 2-1. Refer to **Package Type** for the location of pins.

TABLE 2-1: PIN FUNCTION TABLE

| Pin Number | Pin Name | Description |
|------------|----------|-------------|
| 1 | Source | Source |
| 2 | Gate | Gate |
| 3 | Drain | Drain |

3.0 FUNCTIONAL DESCRIPTION

Figure 3-1 illustrates the switching waveforms and test circuit for VN2410.

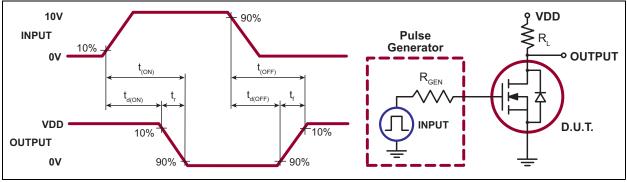


FIGURE 3-1: Switching Waveforms and Test Circuit.

TABLE 3-1: PRODUCT SUMMARY

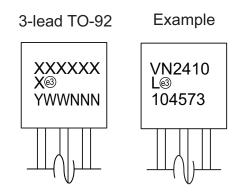
| BV _{DSS} /BV _{DGS} (V) | R _{DS(ON)} (Maximum) (Ω) | I _{DSS} (Minimum) (A) |
|---|---|--------------------------------------|
| 240 | 10 | 1 |

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VN2410

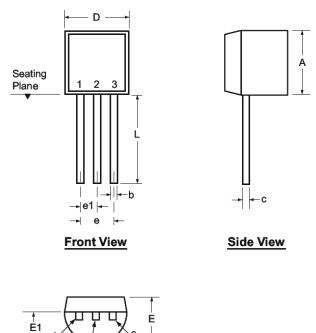
4.0 PACKAGING INFORMATION

4.1 Package Marking Information



| Legend | : XXX Y YY WW NNN @3 * | Product Code or Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC [®] designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package. |
|--------|--|---|
| | be carrie characters | nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for product code or customer-specific information. Package may or e the corporate logo. |

3-Lead TO-92 Package Outline (L/LL/N3)



Bottom View

Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

| Symb | ol | А | b | с | D | E | E1 | е | e1 | L |
|------------------------|-----|------|-------|-------|------|------|------|------|------|-------|
| | MIN | .170 | .014† | .014† | .175 | .125 | .080 | .095 | .045 | .500 |
| Dimensions (inches) | NOM | - | - | - | - | - | - | - | - | - |
| (| MAX | .210 | .022† | .022† | .205 | .165 | .105 | .105 | .055 | .610* |

JEDEC Registration TO-92. * This dimension is not specified in the JEDEC drawing. † This dimension differs from the JEDEC drawing.

Drawings not to scale.

VN2410

NOTES:

APPENDIX A: REVISION HISTORY

Revision A (May 2021)

- Converted and merged Supertex Doc# DSFP-VN2410 to Microchip DS20006534A
- · Changed the package marking format
- Removed 3-lead TO-92 L P002, P003, and P005 media types to align packaging specifications with the actual BQM
- Added section(s) to comply with Microchip formatting standards
- Made minor text changes throughout the document

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PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

| PART NO Device | Packa | | - <u>X</u> - <u>X</u> Environmental Media Type | Examples: | |
|-------------------|---------|----|--|--------------------|--|
| | Optio | ns | | a) VN2410L-G: | N-Channel Enhancement- Mode, Vertical DMOS FET, 3-lead TO-92, 1000/Bag |
| Device: | VN2410 | = | N-Channel Enhancement-Mode Vertical DMOS FET | b) VN2410L-G-P013: | N-Channel Enhancement- Mode, Vertical DMOS FET, |
| Package: | L | = | 3-lead TO-92 | | 3-lead TO-92, 2000/AMMO Pack |
| Environmental: | G | = | Lead (Pb)-free/RoHS-compliant Package | c) VN2410L-G-P014: | N-Channel Enhancement- Mode, Vertical DMOS FET, |
| Media Types: | (blank) | = | 1000/Bag for an L Package | | 3-lead TO-92, 2000/AMMO Pack |
| | P013 | = | 2000/AMMO Pack for an L Package | | |
| | P014 | = | 2000/AMMO Pack for an L Package | | |

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